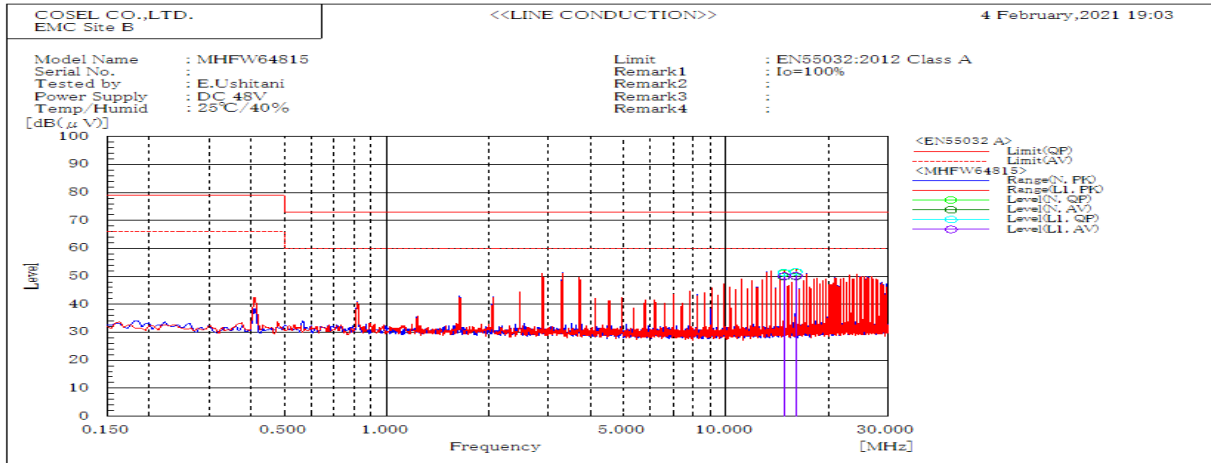
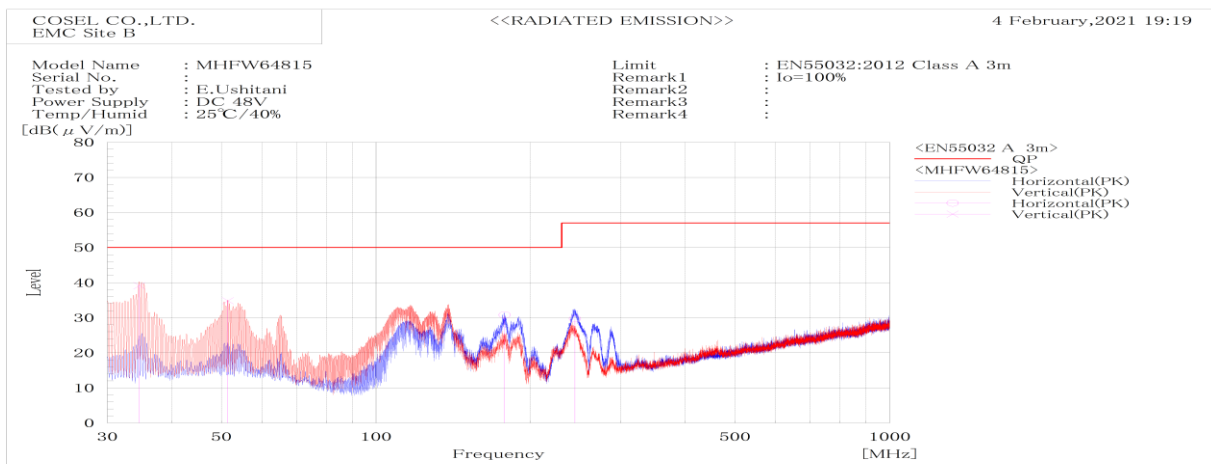


| DATA SHEET | | Date | 05-Nov-21 |
|------------|--|-----------|------------|
| Model | MHFW64815 | Temp. | 25 degreeC |
| Test | EMI Line conduction & Radiated emission | Humid. | 40 %RH |
| | | Tested by | E.Ushitani |



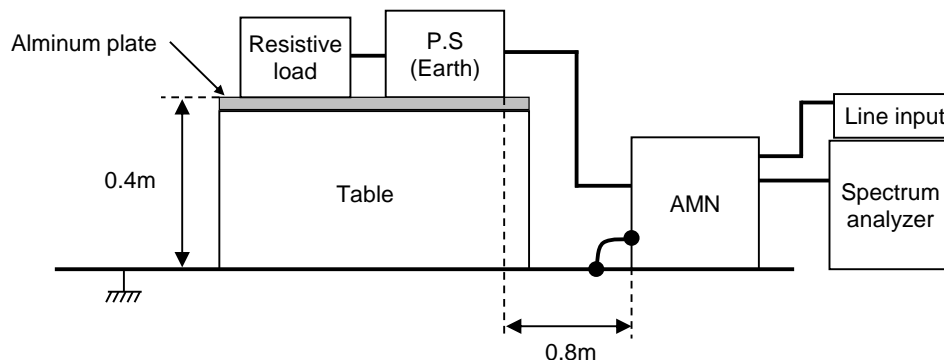
| Frequency MHz | Line | Level dB(μV) | | Limit dB(μV) | | Margin dB | | Pass/Fail | Remark |
|------------------|------|-----------------|------|-----------------|----|--------------|------|-----------|--------|
| | | QP | AV | QP | AV | QP | AV | | |
| 16.069 | L1 | 51.7 | 50.2 | 73 | 60 | 21.3 | 9.8 | Pass | |
| 14.832 | L1 | 51.4 | 50.1 | 73 | 60 | 21.6 | 9.9 | Pass | |
| 16.067 | N | 51.5 | 50 | 73 | 60 | 21.5 | 10 | Pass | |
| 14.831 | N | 51.2 | 49.9 | 73 | 60 | 21.8 | 10.1 | Pass | |



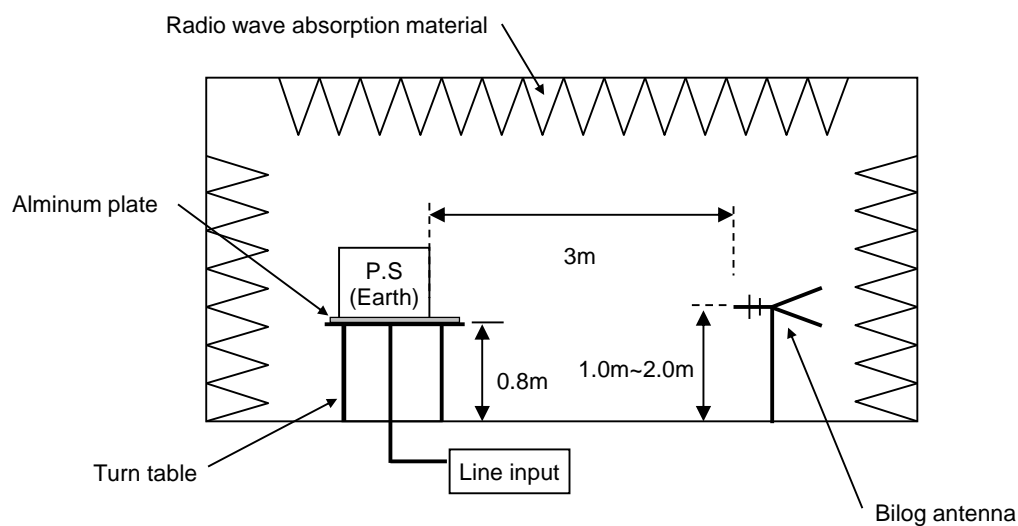
| Frequency MHz | Polarization | Stability | Level dB(μV/m) | Limit dB(μV/m) | Margin dB | Pass/Fail | Height cm | Angle deg | Remark |
|------------------|--------------|-----------|-------------------|-------------------|--------------|-----------|--------------|--------------|--------|
| | | | QP | QP | QP | | | | |
| 34.62 | V | Stable | 39.1 | 50 | 10.9 | Pass | 100.2 | 0 | |
| 51.505 | V | Stable | 34.8 | 50 | 15.2 | Pass | 100.4 | 332.1 | |
| 178.056 | H | Stable | 30.8 | 50 | 19.2 | Pass | 199.7 | 164.6 | |
| 243.967 | H | Stable | 29.7 | 57 | 27.3 | Pass | 133.2 | 35.8 | |

| DATA SHEET | | Date | 05-Nov-21 |
|------------|--|-----------|------------|
| Model | Circuit used for measurement | Temp. | 25 degreeC |
| Test | EMI Line conduction & Radiated emission | Humid. | 40 %RH |
| | | Tested by | E.Ushitani |

1. Line conduction



2. Radiated emission



Conditions

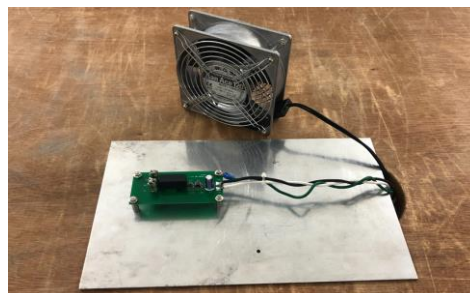
Test : EMI
Model Name: MHFW6□□

○Photographs of Test Set-Up

LINE CONDUCTION



RADIATED EMISSION



○Testing circuitry

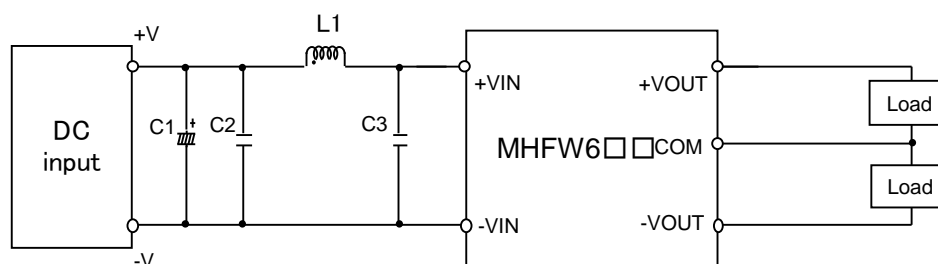


Fig.1 Testing circuitry

| | | |
|------|-----------|---|
| C1 : | MHFS612□□ | 50V 100 μ F Electric capacitor (LXZseries NIPPON CHEMI-CON) |
| | MHFS624□□ | - |
| | MHFS648□□ | - |
| C2 : | MHFS612□□ | 25V 10 μ F Ceramic capacitor (GRM31CR71E106K MURATA MANUFACTURING) |
| | MHFS624□□ | 50V 4.7 μ F Ceramic capacitor (GRM31CR71H475K MURATA MANUFACTURING) |
| | MHFS648□□ | 100V 2.2 μ F Ceramic capacitor (HMK316AC7225KLHTE TAIYO YUDEN) |
| C3 : | MHFS612□□ | 25V 10 μ F Ceramic capacitor (GRM31CR71E106K MURATA MANUFACTURING) |
| | MHFS624□□ | 50V 4.7 μ F Ceramic capacitor (GRM31CR71H475K MURATA MANUFACTURING) |
| | MHFS648□□ | 100V 2.2 μ F Ceramic capacitor (HMK316AC7225KLHTE TAIYO YUDEN) |
| L1 : | MHFS612□□ | 2600mA 2.2 μ H Inductor (LQH5BPN2R2NT0 MURATA MANUFACTURING) |
| | MHFS624□□ | 1600mA 10 μ H Inductor (LQH5BPN100MT0 MURATA MANUFACTURING) |
| | MHFS648□□ | 1050mA 22 μ H Inductor (LQH5BPN220MT0 MURATA MANUFACTURING) |